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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE  
JUN 28 2001

#17/Ind C  
A. Ford  
6/30/01

In re the Application of: Naoya SASHIDA et al. TECHNOLOGY CENTER 2800

Serial Number: 09/321,605

Group Art Unit: 2813

Filed: May 28, 1999

Examiner: Chen, J.

For: METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE HAVING CAPACITOR (as amended)

AMENDMENT

Director of Patents and Trademarks  
Washington, D.C. 20231

June 25, 2001

Dear Sir:

In response to the Office Action dated February 23, 2001, please reconsider the above-identified application amended as follows:

IN THE CLAIMS:

Please amend claims 1, 2, 14 and 21 as follows:

1. (Twice Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming an impurity diffusion layer in a semiconductor substrate;

forming a first insulating film covering the semiconductor substrate;

forming a lower electrode of a capacitor on the first insulating film;

forming an oxide dielectric film of the capacitor on the lower electrode;

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